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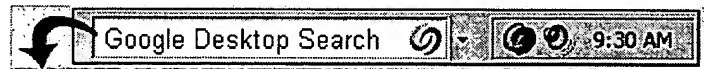
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L5 L3 and substrate 1 L5

L4 L3 asnd substrate 253022 L4

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L2 L1 and "shield electrode" 1 L2

L1 20050167695 1 L1

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<u>L6</u>	JFET and "field shield"	2	<u>L6</u>
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<u>L5</u>	L3 and substrate	1	<u>L5</u>
<u>L4</u>	L3 asnd substrate	253022	<u>L4</u>
<u>L3</u>	L2	1	<u>L3</u>
<u>L2</u>	L1 and "shield electrode"	1	<u>L2</u>
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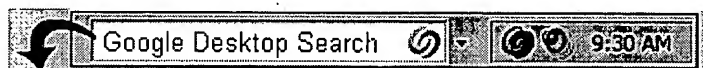
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